

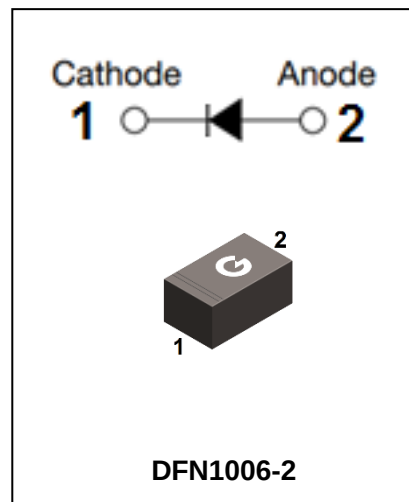
Silicon Epitaxial Planar Diode

BAV16L

FEATURES

- Fast Switching Speed: $t_{rr} = 4\text{ns}$ (Typ.)
- Surface Mount Package Ideally Suited For Automatic Insertion
- For General Purpose Switching Applications
- High Conductance
- RoHS compliant with Halogen-free

HF



APPLICATIONS

- Surface mount fast switching diode

ORDERING INFORMATION

Type No.	Marking	Package Code
BAV16L	T6	DFN1006-2

MAXIMUM RATING @ $T_a=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Reverse Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_o	150	mA
Non-Repetitive Peak Forward Surge Current @ $t=1.0\ \mu\text{s}$ @ $t=1.0\ \text{s}$	I_{FSM}	2.0 1.0	A
Power Dissipation	P_d	200	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	375	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	$^\circ\text{C}$

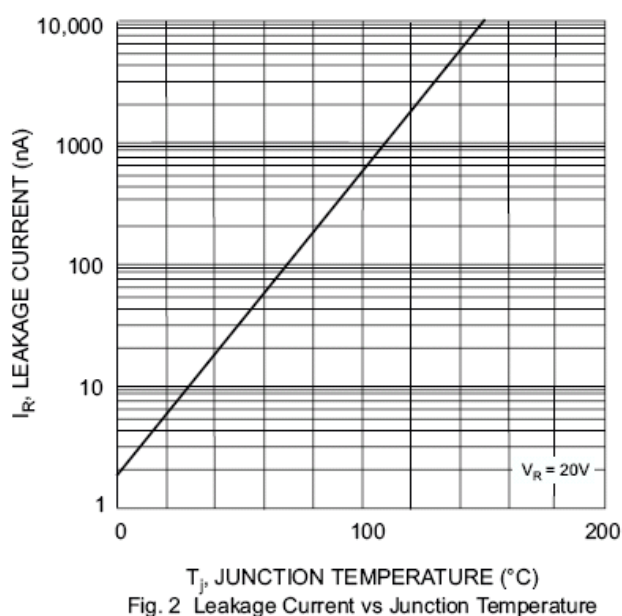
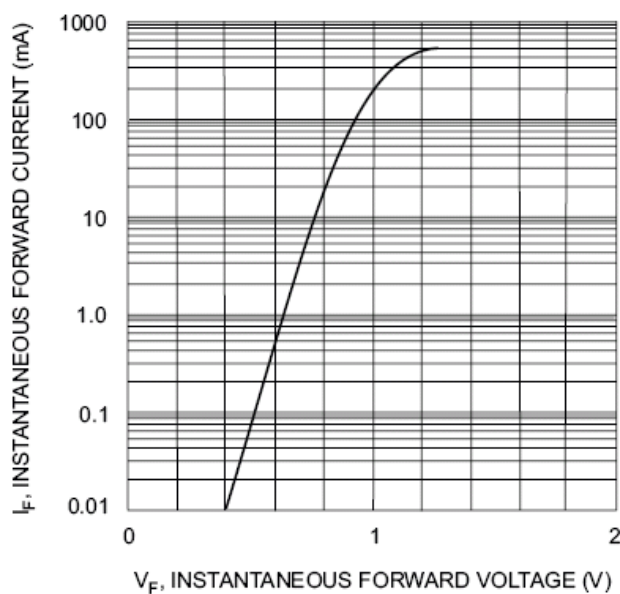
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ELECTRICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
Reverse Breakdown Voltage	$V_{(BR)R}$	75	-	V	$I_R=1.0\mu A$
Forward Voltage	V_F		0.715 0.855 1.0 1.25	V	$I_F=1mA$ $I_F=10mA$ $I_F=50mA$ $I_F=150mA$
Reverse Current	I_R	-	1.0 25	μA nA	$V_R=75V$ $V_R=20V$
Capacitance between terminals	C_T	-	2.0	pF	$V_R=0, f=1.0MHz$
Reverse Recovery Time	t_{rr}	-	4.0	ns	$I_F=I_R=10mA$, $I_{rr}=0.1\times I_R, R_L=100\Omega$

TYPICAL CHARACTERISTICS @ Ta=25°C unless otherwise specified



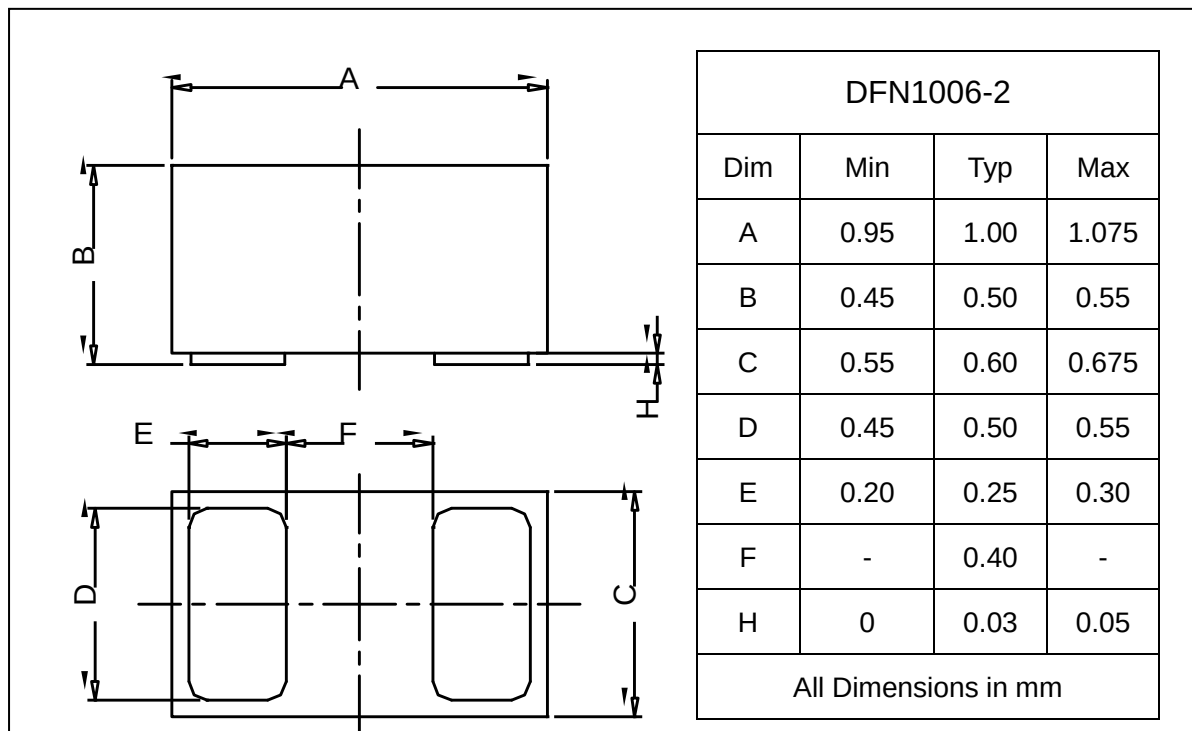
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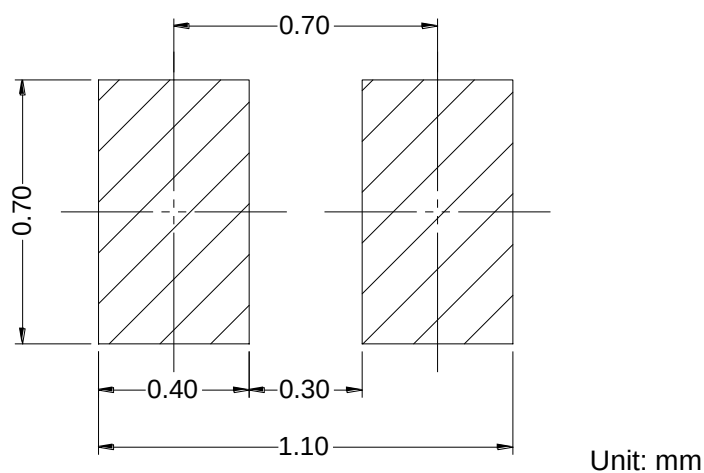
PACKAGE OUTLINE

Plastic surface mounted package

DFN1006-2



SOLDERING FOOTPRINT



PACKAGE INFORMATION

Device	Package	Shipping
BAV16L	DFN1006-2	10000 pcs / Tape & Reel